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Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Sheet 1 of 2

Complete if Known

Application Number	10/086,621
Filing Date	March 4, 2002
First Named Inventor	Valery KAGADEI, et al.
Group Art Unit	2838
Confirmation No.	6897

Attorney Docket Number KAGADEI=1

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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
KF	BB	ANISHCHENKO et al., <i>Dry Cleaning of Fluorocarbon Residues by Atomic Hydrogen Flow</i> , International Conference Micro- and Nanoelectronic, ICMN-2003, (October, 2003), pp. 1-6.	
	BC	ANISHCHENKO et al., <i>Residual Photoresist Removal from Si and GaAs Surface by Atomic Hydrogen Flow Treatment</i> , International Conference Micro- and Nanoelectronic, ICMN-2003, (October, 2003), pp. 1-5.	
	BD	BOZHKOV et al., <i>A Comparative Study of the Atomic Hydrogen Penetration into the Thin Vanadium Films and Silicon Oxide-Gallium Arsenide Structures</i> , <i>Technical Physics Letters</i> , Vol. 26, no. 10 (2000), pp. 926-928.	
	BE	CHALDYSHEV et al., <i>Hydrogenation of GaAs Films Grown at Low Temperature</i> , Symposium on Non-Stoichiometric III-V Compounds, (October, 2001), pp. 1-6.	
	BF	KAGADEI et al., <i>Atomic Hydrogen Flux Density Measured Using Thin Metal Films</i> , <i>Technical Physics Letters</i> , Vol. 29, no. 11 (2003), pp. 897-900.	
	BG	KAGADEI et al., <i>Current-Voltage Characteristics of a Reflex Discharge with a Hollow Cathode and Self-Heating Electrode</i> , <i>Technical Physics</i> , Vol. 46, no. 3 (2001), pp. 292-298. Published in Mar 01	
	BH	KAGADEI et al., <i>The Effect of Atomic Hydrogen Flow on Electrical Resistance of the Transition Metal Films</i> , The European Material Conference, E-MRS, (June, 2003), pp. 1-15.	
	BI	KAGADEI et al., <i>The Effect of Hydrogenation on the Photoconductivity of Ion-Doped Gallium Arsenide Structures</i> , <i>Technical Physics Letters</i> , Vol. 26, no. 4 (2000), pp. 269-271.	
	BJ	KAGADEI et al., <i>The Effect of Hydrogenation on the Sink Breakdown Voltage of Transistors Based on Ion-Doped Gallium Arsenide Structures</i> , <i>Technical Physics Letters</i> , Vol. 29, no. 1 (2003), pp. 12-15.	
	BK	KAGADEI et al., <i>Hydrogenation Kinetics and Change in Resistance of Thin Vanadium Films Under Treatment by Atomic Hydrogen Flow</i> , <i>Izvestiya Vysshikh Uchebykh Zavedenii, Fizika</i> , no. 11 (2003), pp. 67-76. (Abstract only)	YES
	BL	KAGADEI et al., <i>In situ Cleaning of GaAs and Al_xGa_{1-x}As Surfaces and Production of Ohmic Contacts using an Atomic Hydrogen Source Based on a Reflected Arc Discharge</i> , <i>Journal of Vacuum Technology</i> , Vol. 17 (1999), pp. 1488-1493.	
KF	BM	KAGADEI et al., <i>Investigation of the Penetration of Atomic Hydrogen from the Gas Phase into SiO₂/GaAs</i> , <i>Journal of Vacuum Technology</i> , Vol. 19 (2001), pp. 1871-1877	

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Sheet

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3

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Group Art Unit	
Examiner Name	

Attorney Docket Number

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AC	LEONE, "Kinetic-Energy-Enhanced Neutral Etching", <u>Jpn. J. Appl. Phys.</u> , (1995), vol. 34, No. 4B, pages 2073-2082		
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AK	WOLAN et al., "Chemical reactions induced by the room temperature interaction of hyperthermal atomic hydrogen with the native oxide layer on GaAs(001) surfaces studied by Ion scattering spectroscopy and X-ray photoelectron spectroscopy", <u>J. Vac. Sci. Technol.</u> , (1997), vol 15, No. 5, pages 2502-2507		
AL	KORZEC et al. "Characterization of a slot antenna microwave plasma source for hydrogen plasma cleaning", <u>J. Vac. Sci Technol.</u> , (1995), vol. 13, No. 4, page 2074-2085		
AM	EPI MBE Production Group. Aug./Sept., 1994, Applications Note, "On the Use of Atomic Hydrogen in MBE"		
AN	Application Note, "Cracking Efficiency of the EPI Atomic Hydrogen Source", EPI, January, 1996, No. 1/96		

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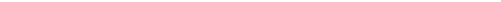
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		Filing Date	March 4, 2002
		First Named Inventor	Valery KAGADEI, et al.
		Group Art Unit	2838
		Confirmation No.	6897
Sheet	2	of	2
		Attorney Docket Number	KAGADEI-1

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**INFORMATION DISCLOSURE
 STATEMENT BY APPLICANT**
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Sheet 3 of 3

Compleat if Known	
Application Number	10/086,621
Filing Date	March 4, 2002
First Named Inventor	V. KAGADEI et al.
Group Art Unit	
Examiner Name	
Attorney Docket Number	KAGADEI=1

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
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PF	AO	LIVSHITS et al., "Dissociation of hydrogen molecules on Metal filaments in H ⁺ ion sources", <u>Plasma Source Sci. Technol.</u> , (1994), pages 465-472	
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	AR	GEDDES et al., "Dissociation for hydrogen in High frequency discharges", <u>Plasma Source Sci. Technol.</u> , (1993), vol. 2, pages 93-99	
	AS	RF Gas Cracker/Reactives Atom Source - HD Series, The product of Oxford Applied Research	
	AT	GOODMAN et al., "Ar, N ₂ , and Cl ₂ electron cyclotron resonance plasma measured by time-of-flight analysis: Neutral kinetic energies and source gas cracking", <u>J. Vac. Sci. Technol.</u> , (1997), B vol. 15, No. 4, pages 971-982	
	AU	SHERMAN, "In Situ removal of native oxide from silicon wafers", <u>J. Vac. Sci. Technol.</u> , B vol. 8, No. 4, pages 655-657	
	AV	SAMANO et al., "An arc discharge hydrogen atom source", <u>Rev. Sci. Instrum.</u> , (1993), vol. 64, No. 10, pages 2746-2752	
	AW	GORRIER et al., "Growth of Dielectric Films of Semiconductors and Metals Using a Multipole Plasma", <u>Thin Solid Films</u> , (1981), vol. 84, Pages 379-388	
	AY	Handbook of Ion Sources, Ed. by Bernard Wolf, CRC Press, (1995), Pages 32-34, 54-56, 61, 69-71, 222-223	
	AZ	GABOVICH et al., "Out of plasma with high concentration of concentration of charged particles into vacuum", <u>Journal of Technical Physics</u> , (1961), vol. 31, No. 9, Pages 1049-1055	XXX
PF	BA	ITO et al., "Purification of diamond films by applying current into the plasma stream in the arc discharge plasma jet chemical vapor deposition technique", <u>J. Appl. Phys.</u> , (1995), vol. 77, No. 12, Pages 6636-6640	

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PTO/SB/57 (10/86)

Substitute for form 1463A PTO
3 TRANSINFORMATION DISCLOSURE
STATEMENT BY APPLICANT

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Sheet

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Complete if Known

Application Number	10/086,621
Filing Date	March 4, 2002
First Named Inventor	V. KAGADEI et al.
Group Art Unit	
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Attorney Docket Number KAGADEI=1

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
PP	AC	LEONE, "Kinetic-Energy-Enhanced Neutral Etching", <u>Jpn. J. Appl. Phys.</u> , (1995), vol. 34, No. 4B, pages 20-73-2082	
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1 JUN 18 2002

PTO/SB/57 (10/98)

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TRADEINFORMATION DISCLOSURE
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Sheet

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Application Number	10/086,621
Filing Date	March 4, 2002
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Group Art Unit	
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KAGADEI=1

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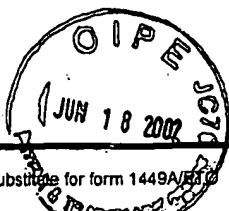
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Group Art Unit

Examiner Name

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U.S. PATENT DOCUMENTS

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